

Daniele Ercolani

List of Publications by Citations

Source: <https://exaly.com/author-pdf/8404915/daniele-ercolani-publications-by-citations.pdf>

Version: 2024-04-28

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

102
papers

2,085
citations

25
h-index

40
g-index

114
ext. papers

2,373
ext. citations

6.2
avg. IF

4.54
L-index

| # | Paper | IF | Citations |
|-----|--|------|-----------|
| 102 | Ultrafast multi-terahertz nano-spectroscopy with sub-cycle temporal resolution. <i>Nature Photonics</i> , 2014 , 8, 841-845 | 33.9 | 171 |
| 101 | Room-temperature terahertz detectors based on semiconductor nanowire field-effect transistors. <i>Nano Letters</i> , 2012 , 12, 96-101 | 11.5 | 145 |
| 100 | InAs/InSb nanowire heterostructures grown by chemical beam epitaxy. <i>Nanotechnology</i> , 2009 , 20, 505605 | 3.4 | 112 |
| 99 | Unit cell structure of crystal polytypes in InAs and InSb nanowires. <i>Nano Letters</i> , 2011 , 11, 1483-9 | 11.5 | 110 |
| 98 | Strain induced effects on the transport properties of metamorphic InAlAs/InGaAs quantum wells. <i>Thin Solid Films</i> , 2005 , 484, 400-407 | 2.2 | 66 |
| 97 | Giant thermovoltage in single InAs nanowire field-effect transistors. <i>Nano Letters</i> , 2013 , 13, 3638-42 | 11.5 | 48 |
| 96 | Faceting of InAs/InSb Heterostructured Nanowires. <i>Crystal Growth and Design</i> , 2010 , 10, 4038-4042 | 3.5 | 47 |
| 95 | Controlling the diameter distribution and density of InAs nanowires grown by Au-assisted methods. <i>Semiconductor Science and Technology</i> , 2015 , 30, 115012 | 1.8 | 44 |
| 94 | Growth of InAs/InAsSb heterostructured nanowires. <i>Nanotechnology</i> , 2012 , 23, 115606 | 3.4 | 43 |
| 93 | Nanoscale spin rectifiers controlled by the Stark effect. <i>Nature Nanotechnology</i> , 2014 , 9, 997-1001 | 28.7 | 42 |
| 92 | Manipulation of electron orbitals in hard-wall InAs/InP nanowire quantum dots. <i>Nano Letters</i> , 2011 , 11, 1695-9 | 11.5 | 41 |
| 91 | Semiconductor nanowires for highly sensitive, room-temperature detection of terahertz quantum cascade laser emission. <i>Applied Physics Letters</i> , 2012 , 100, 241101 | 3.4 | 37 |
| 90 | Thermoelectric Conversion at 30 K in InAs/InP Nanowire Quantum Dots. <i>Nano Letters</i> , 2019 , 19, 3033-3039 | 3.5 | 34 |
| 89 | Nanowire-based field effect transistors for terahertz detection and imaging systems. <i>Nanotechnology</i> , 2013 , 24, 214005 | 3.4 | 33 |
| 88 | Modeling of InAs-InSb nanowires grown by Au-assisted chemical beam epitaxy. <i>Nanotechnology</i> , 2012 , 23, 095602 | 3.4 | 33 |
| 87 | Readsorption Assisted Growth of InAs/InSb Heterostructured Nanowire Arrays. <i>Crystal Growth and Design</i> , 2013 , 13, 878-882 | 3.5 | 32 |
| 86 | Hot-electron effects in InAs nanowire Josephson junctions. <i>Nano Research</i> , 2011 , 4, 259-265 | 10 | 32 |

| | | | |
|----|---|------|----|
| 85 | Near-field terahertz probes with room-temperature nanodetectors for subwavelength resolution imaging. <i>Scientific Reports</i> , 2017 , 7, 44240 | 4.9 | 30 |
| 84 | Pb/InAs nanowire Josephson junction with high critical current and magnetic flux focusing. <i>Nano Letters</i> , 2015 , 15, 1803-8 | 11.5 | 29 |
| 83 | Growth of defect-free GaP nanowires. <i>Nanotechnology</i> , 2014 , 25, 205601 | 3.4 | 28 |
| 82 | Length distributions of Au-catalyzed and In-catalyzed InAs nanowires. <i>Nanotechnology</i> , 2016 , 27, 375602 | 3.4 | 27 |
| 81 | Electronic properties of quantum dot systems realized in semiconductor nanowires. <i>Semiconductor Science and Technology</i> , 2010 , 25, 024007 | 1.8 | 27 |
| 80 | Tunable Esaki Effect in Catalyst-Free InAs/GaSb Core-Shell Nanowires. <i>Nano Letters</i> , 2016 , 16, 7950-7955 | 11.5 | 26 |
| 79 | Magnetically-driven colossal supercurrent enhancement in InAs nanowire Josephson junctions. <i>Nature Communications</i> , 2017 , 8, 14984 | 17.4 | 25 |
| 78 | Catalyst-free growth of InAs nanowires on Si (111) by CBE. <i>Nanotechnology</i> , 2015 , 26, 415604 | 3.4 | 25 |
| 77 | Ionic-Liquid Gating of InAs Nanowire-Based Field-Effect Transistors. <i>Advanced Functional Materials</i> , 2019 , 29, 1804378 | 15.6 | 25 |
| 76 | Se-doping dependence of the transport properties in CBE-grown InAs nanowire field effect transistors. <i>Nanoscale Research Letters</i> , 2012 , 7, 159 | 5 | 24 |
| 75 | Electrostatic spin control in InAs/InP nanowire quantum dots. <i>Nano Letters</i> , 2012 , 12, 4490-4 | 11.5 | 24 |
| 74 | Terahertz detection by heterostructured InAs/InSb nanowire based field effect transistors. <i>Applied Physics Letters</i> , 2012 , 101, 141103 | 3.4 | 23 |
| 73 | Catalyst Composition Tuning: The Key for the Growth of Straight Axial Nanowire Heterostructures with Group III Interchange. <i>Nano Letters</i> , 2016 , 16, 7183-7190 | 11.5 | 22 |
| 72 | Complete thermoelectric benchmarking of individual InSb nanowires using combined micro-Raman and electric transport analysis. <i>Nano Research</i> , 2015 , 8, 4048-4060 | 10 | 22 |
| 71 | Local noise in a diffusive conductor. <i>Scientific Reports</i> , 2016 , 6, 30621 | 4.9 | 21 |
| 70 | Crystal phase induced bandgap modifications in AlAs nanowires probed by resonant Raman spectroscopy. <i>ACS Nano</i> , 2013 , 7, 1400-7 | 16.7 | 21 |
| 69 | Raman sensitivity to crystal structure in InAs nanowires. <i>Applied Physics Letters</i> , 2012 , 100, 143101 | 3.4 | 20 |
| 68 | Gate-Tunable Spatial Modulation of Localized Plasmon Resonances. <i>Nano Letters</i> , 2016 , 16, 5688-93 | 11.5 | 20 |

| | | | |
|----|--|------|----|
| 67 | Detection of a 2.8 THz quantum cascade laser with a semiconductor nanowire field-effect transistor coupled to a bow-tie antenna. <i>Applied Physics Letters</i> , 2014 , 104, 083116 | 3.4 | 19 |
| 66 | Pd-Assisted Growth of InAs Nanowires. <i>Crystal Growth and Design</i> , 2010 , 10, 4197-4202 | 3.5 | 19 |
| 65 | InAs/InP/InSb Nanowires as Low Capacitance nB Heterojunction Diodes. <i>Physical Review X</i> , 2011 , 1, | 9.1 | 19 |
| 64 | Nucleation and growth mechanism of self-catalyzed InAs nanowires on silicon. <i>Nanotechnology</i> , 2016 , 27, 255601 | 3.4 | 19 |
| 63 | Electronic band structure of wurtzite GaP nanowires via temperature dependent resonance Raman spectroscopy. <i>Applied Physics Letters</i> , 2013 , 103, 023108 | 3.4 | 18 |
| 62 | Suppression of lateral growth in InAs/InAsSb heterostructured nanowires. <i>Journal of Crystal Growth</i> , 2013 , 366, 8-14 | 1.6 | 18 |
| 61 | Scattering mechanisms in undoped In _{0.75} Ga _{0.25} As/In _{0.75} Al _{0.25} As two-dimensional electron gases. <i>Journal of Crystal Growth</i> , 2005 , 278, 538-543 | 1.6 | 18 |
| 60 | Coexistence of vapor-liquid-solid and vapor-solid-solid growth modes in Pd-assisted InAs nanowires. <i>Small</i> , 2010 , 6, 1935-41 | 11 | 17 |
| 59 | Transport anisotropy in In _{0.75} Ga _{0.25} As two-dimensional electron gases induced by indium concentration modulation. <i>Physical Review B</i> , 2008 , 77, | 3.3 | 16 |
| 58 | Desorption dynamics of oxide nanostructures fabricated by local anodic oxidation nanolithography. <i>Journal of Applied Physics</i> , 2005 , 97, 114324 | 2.5 | 16 |
| 57 | Nanoparticle Stability in Axial InAs-InP Nanowire Heterostructures with Atomically Sharp Interfaces. <i>Nano Letters</i> , 2018 , 18, 167-174 | 11.5 | 16 |
| 56 | Nanowire Terahertz detectors with a resonant four-leaf-clover-shaped antenna. <i>Optics Express</i> , 2014 , 22, 8996-9003 | 3.3 | 15 |
| 55 | Hall nano-probes fabricated by focused ion beam. <i>Nanotechnology</i> , 2006 , 17, 2105-2109 | 3.4 | 15 |
| 54 | Self-Assembled InAs Nanowires as Optical Reflectors. <i>Nanomaterials</i> , 2017 , 7, | 5.4 | 14 |
| 53 | Suspended InAs nanowire Josephson junctions assembled via dielectrophoresis. <i>Nanotechnology</i> , 2015 , 26, 385302 | 3.4 | 13 |
| 52 | One dimensional semiconductor nanostructures: An effective active-material for terahertz detection. <i>APL Materials</i> , 2015 , 3, 026104 | 5.7 | 13 |
| 51 | Terahertz photodetectors based on tapered semiconductor nanowires. <i>Applied Physics Letters</i> , 2014 , 105, 231112 | 3.4 | 13 |
| 50 | Growth mechanism of InAsInSb heterostructured nanowires grown by chemical beam epitaxy. <i>Journal of Crystal Growth</i> , 2011 , 323, 304-306 | 1.6 | 13 |

| | | | |
|----|---|------|----|
| 49 | Assessing the thermoelectric properties of single InSb nanowires: the role of thermal contact resistance. <i>Semiconductor Science and Technology</i> , 2016 , 31, 064001 | 1.8 | 13 |
| 48 | Electron beam induced current in InSb-InAs nanowire type-III heterostructures. <i>Applied Physics Letters</i> , 2012 , 101, 063116 | 3.4 | 12 |
| 47 | GaAs Oxide Desorption under Extreme Ultraviolet Photon Flux. <i>Advanced Functional Materials</i> , 2005 , 15, 587-592 | 15.6 | 11 |
| 46 | Suspended InAs Nanowire-Based Devices for Thermal Conductivity Measurement Using the 3 ω Method. <i>Journal of Materials Engineering and Performance</i> , 2018 , 27, 6299-6305 | 1.6 | 11 |
| 45 | Growth dynamics of InAs/InP nanowire heterostructures by Au-assisted chemical beam epitaxy. <i>Nanotechnology</i> , 2019 , 30, 094003 | 3.4 | 10 |
| 44 | Charge localization and reentrant superconductivity in a quasi-ballistic InAs nanowire coupled to superconductors. <i>Science Advances</i> , 2019 , 5, eaav1235 | 14.3 | 10 |
| 43 | Towards a Hybrid High Critical Temperature Superconductor Junction With a Semiconducting InAs Nanowire Barrier. <i>Journal of Superconductivity and Novel Magnetism</i> , 2015 , 28, 3429-3437 | 1.5 | 10 |
| 42 | Large thermal biasing of individual gated nanostructures. <i>Nano Research</i> , 2014 , 7, 579-587 | 10 | 10 |
| 41 | Synthesis of AlAs and AlAs/GaAs Core/Shell Nanowires. <i>Crystal Growth and Design</i> , 2011 , 11, 4053-4058 | 3.5 | 10 |
| 40 | Noise thermometry applied to thermoelectric measurements in InAs nanowires. <i>Semiconductor Science and Technology</i> , 2016 , 31, 104001 | 1.8 | 10 |
| 39 | Orbital Tuning of Tunnel Coupling in InAs/InP Nanowire Quantum Dots. <i>Nano Letters</i> , 2020 , 20, 1693-1699 | 11.5 | 9 |
| 38 | GHz Electroluminescence Modulation in Nanoscale Subwavelength Emitters. <i>Nano Letters</i> , 2016 , 16, 5521-7 | 11.5 | 9 |
| 37 | Strain-induced band alignment in wurtzite/zinc-blende InAs heterostructured nanowires. <i>Physical Review B</i> , 2015 , 92, | 3.3 | 9 |
| 36 | Evidence of material mixing during local anodic oxidation nanolithography. <i>Journal of Applied Physics</i> , 2005 , 98, 114303 | 2.5 | 9 |
| 35 | The graphon-polyelectrolytes interface as a model for coal slurries. <i>Colloids and Surfaces</i> , 1990 , 48, 231-241 | | 9 |
| 34 | InAs nanowire superconducting tunnel junctions: Quasiparticle spectroscopy, thermometry, and nanorefrigeration. <i>Nano Research</i> , 2017 , 10, 3468-3475 | 10 | 8 |
| 33 | Raman scattering study of InAs nanowires under high pressure. <i>Nanotechnology</i> , 2014 , 25, 465704 | 3.4 | 8 |
| 32 | Chemistry and formation process of Ga(Al)As oxide during local anodic oxidation nanolithography. <i>Surface Science</i> , 2006 , 600, 3739-3743 | 1.8 | 8 |

| | | | |
|----|--|------|---|
| 31 | Magnetic field and temperature dependence of an atomic force microscope-defined quantum point contact. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2004 , 22, 570 | | 8 |
| 30 | Strong Modulations of Optical Reflectance in Tapered Core-Shell Nanowires. <i>Materials</i> , 2019 , 12, | 3.5 | 8 |
| 29 | Heterogeneous nucleation of catalyst-free InAs nanowires on silicon. <i>Nanotechnology</i> , 2017 , 28, 065603 | 3.4 | 6 |
| 28 | Electrical probing of carrier separation in InAs/InP/GaAsSb core-dualshell nanowires. <i>Nano Research</i> , 2020 , 13, 1065-1070 | 10 | 6 |
| 27 | Large-area ohmic top contact to vertically grown nanowires using a free-standing Au microplate electrode. <i>ACS Applied Materials & Interfaces</i> , 2012 , 4, 1860-4 | 9.5 | 6 |
| 26 | X-ray induced variation of the chemistry of GaAs/AlAs oxide nanostructures. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2006 , 246, 39-44 | 1.2 | 6 |
| 25 | Laser induced photothermal effects on InAs nanowires: tuning the hole density. <i>Journal of Materials Chemistry C</i> , 2016 , 4, 2339-2344 | 7.1 | 5 |
| 24 | Internal field induced enhancement and effect of resonance in Raman scattering of InAs nanowires. <i>Solid State Communications</i> , 2013 , 160, 26-31 | 1.6 | 5 |
| 23 | LEEM and XPEEM studies of C-AFM induced surface modifications of thermally grown SiO ₂ . <i>Journal of Electron Spectroscopy and Related Phenomena</i> , 2005 , 144-147, 1163-1166 | 1.7 | 5 |
| 22 | Growth and Strain Relaxation Mechanisms of InAs/InP/GaAsSb Core-Dual-Shell Nanowires. <i>Crystal Growth and Design</i> , 2020 , 20, 1088-1096 | 3.5 | 5 |
| 21 | Crystal Phases in Hybrid Metal-Semiconductor Nanowire Devices. <i>Nano Letters</i> , 2017 , 17, 2336-2341 | 11.5 | 4 |
| 20 | Morphology control of single-crystal InSb nanostructures by tuning the growth parameters. <i>Nanotechnology</i> , 2020 , 31, 384002 | 3.4 | 4 |
| 19 | Mapping of axial strain in InAs/InSb heterostructured nanowires. <i>Applied Physics Letters</i> , 2015 , 107, 093102 | 1.4 | 4 |
| 18 | Electrostatic spin control in multi-barrier nanowires. <i>Journal Physics D: Applied Physics</i> , 2014 , 47, 394015 | 3 | 4 |
| 17 | Behavior of SiO ₂ nanostructures under intense extreme ultraviolet illumination. <i>Journal of Applied Physics</i> , 2005 , 97, 104333 | 2.5 | 4 |
| 16 | Type II band alignment in InAs zinc-blende/wurtzite heterostructured nanowires. <i>Nanotechnology</i> , 2016 , 27, 415201 | 3.4 | 4 |
| 15 | III-V semiconductor nanostructures and iontronics: InAs nanowire-based electric double layer field effect transistors 2019 , | | 3 |
| 14 | Electrical properties and band diagram of InSb-InAs nanowire type-III heterojunctions. <i>Journal of Applied Physics</i> , 2013 , 113, 104307 | 2.5 | 3 |

| | | | |
|----|---|------|---|
| 13 | Focused ion beam patterned Hall nano-sensors. <i>Journal of Magnetism and Magnetic Materials</i> , 2007 , 310, 2752-2754 | 2.8 | 3 |
| 12 | Transport anisotropy in InGaAs 2D electron gases. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2008 , 40, 1392-1394 | 3 | 3 |
| 11 | Self-Catalyzed InSb/InAs Quantum Dot Nanowires. <i>Nanomaterials</i> , 2021 , 11, | 5.4 | 3 |
| 10 | High-performance room-temperature THz nanodetectors with a narrowband antenna 2014 , | | 2 |
| 9 | High-Mobility Free-Standing InSb Nanoflags Grown on InP Nanowire Stems for Quantum Devices. <i>ACS Applied Nano Materials</i> , 2021 , 4, 5825-5833 | 5.6 | 2 |
| 8 | Mapping the Coulomb Environment in Interference-Quenched Ballistic Nanowires. <i>Nano Letters</i> , 2018 , 18, 124-129 | 11.5 | 2 |
| 7 | Semiconductor nanowire field-effect transistors: towards high-frequency THz detectors 2012 , | | 1 |
| 6 | 2013 , | | 1 |
| 5 | Field Effect Transistors: Ionic-Liquid Gating of InAs Nanowire-Based Field-Effect Transistors (Adv. Funct. Mater. 3/2019). <i>Advanced Functional Materials</i> , 2019 , 29, 1970014 | 15.6 | 1 |
| 4 | Ionic Liquid Gating of Semiconductor Nanostructure-Based Devices. <i>Proceedings (mdpi)</i> , 2019 , 3, 5 | 0.3 | |
| 3 | Rapid method for the interconnection of single nano-objects. <i>Materials Research Express</i> , 2015 , 2, 055011.7 | | |
| 2 | Manipulation of polarization anisotropy in bare InAs and InAs/GaSb core-shell nanowires. <i>Applied Physics Letters</i> , 2018 , 112, 153104 | 3.4 | |
| 1 | Ultrafast Infrared Nanoscopy with Sub-Cycle Temporal Resolution. <i>Microscopy and Microanalysis</i> , 2015 , 21, 2163-2164 | 0.5 | |